

General Purpose Transistors

PNP Silicon

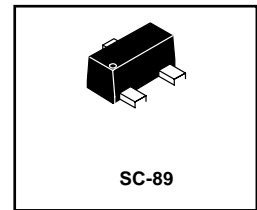
FEATURE

- Simplifies Circuit Design.
- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

LMBT3906TT1G
S-LMBT3906TT1G

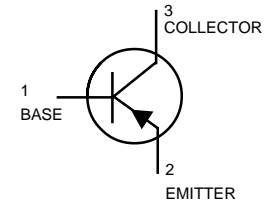
ORDERING INFORMATION

| Device | Marking | Shipping |
|--------------------------------|----------|-------------------|
| LMBT3906TT1G S-LMBT3906TT1G | 2A 2A | 3000/Tape & Reel |
| LMBT3906TT3G S-LMBT3906TT3G | 2A 2A | 10000/Tape & Reel |



MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--------------------------------|-----------|-------|------|
| Collector–Emitter Voltage | V_{CEO} | - 40 | Vdc |
| Collector–Base Voltage | V_{CBO} | - 40 | Vdc |
| Emitter–Base Voltage | V_{EBO} | - 5.0 | Vdc |
| Collector Current — Continuous | I_C | - 200 | mAdc |



THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|-------------|---------------------------|
| Total Device Dissipation FR-4 Board(1) $T_A = 25^\circ\text{C}$ | P_D | 200 | mW |
| Derate above 25°C | | 1.6 | mW/ $^\circ\text{C}$ |
| Thermal Resistance Junction to Ambient | $R_{\theta JA}$ | 600 | $^\circ\text{C}/\text{W}$ |
| Total Device Dissipation FR-4 Board (2), $T_A = 25^\circ\text{C}$ | P_D | 300 | mW |
| Derate above 25°C | | 2.4 | mW/ $^\circ\text{C}$ |
| Thermal Resistance Junction to Ambient | $R_{\theta JA}$ | 400 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

DEVICE MARKING

LMBT3906TT1G = 2A

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|----------------|--------|-----|-----|------|
|----------------|--------|-----|-----|------|

OFF CHARACTERISTICS

| | | | | |
|---|---------------|-------|------|------|
| Collector–Emitter Breakdown Voltage (3) ($I_C = -1.0 \text{ mAdc}, I_B = 0$) | $V_{(BR)CEO}$ | - 40 | — | Vdc |
| Collector–Base Breakdown Voltage ($I_C = -10 \mu\text{Adc}, I_E = 0$) | $V_{(BR)CBO}$ | - 40 | — | Vdc |
| Emitter–Base Breakdown Voltage ($I_E = -10 \mu\text{Adc}, I_C = 0$) | $V_{(BR)EBO}$ | - 5.0 | — | Vdc |
| Base Cutoff Current ($V_{CE} = -30 \text{ Vdc}, V_{EB} = -3.0 \text{ Vdc}$) | I_{BL} | — | - 50 | nAdc |
| Collector Cutoff Current ($V_{CE} = -30 \text{ Vdc}, V_{EB} = -3.0 \text{ Vdc}$) | I_{CEX} | — | - 50 | nAdc |

1. FR-4 Minimum Pad.
2. FR-4 1.0 x 1.0 Inch Pad.
3. Pulse Width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

LMBT3906TT1G;S-LMBT3906TT1G
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

| Characteristic | Symbol | Min | Max | Unit |
|--|---------------|-------|-------|------|
| ON CHARACTERISTICS (3) | | | | |
| DC Current Gain ($I_C = -0.1 \text{ mAdc}$, $V_{CE} = -1.0 \text{ Vdc}$) | h_{FE} | 60 | — | — |
| ($I_C = -1.0 \text{ mAdc}$, $V_{CE} = -1.0 \text{ Vdc}$) | | 80 | — | |
| ($I_C = -10 \text{ mAdc}$, $V_{CE} = -1.0 \text{ Vdc}$) | | 100 | 300 | |
| ($I_C = -50 \text{ mAdc}$, $V_{CE} = -1.0 \text{ Vdc}$) | | 60 | — | |
| ($I_C = -100 \text{ mAdc}$, $V_{CE} = -1.0 \text{ Vdc}$) | | 30 | — | |
| Collector-Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}$, $I_B = -1.0 \text{ mAdc}$) | $V_{CE(sat)}$ | — | -0.25 | Vdc |
| ($I_C = -50 \text{ mAdc}$, $I_B = -5.0 \text{ mAdc}$) | | — | -0.4 | |
| Base-Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}$, $I_B = -1.0 \text{ mAdc}$) | $V_{BE(sat)}$ | -0.65 | -0.85 | Vdc |
| ($I_C = -50 \text{ mAdc}$, $I_B = -5.0 \text{ mAdc}$) | | — | -0.95 | |

SMALL-SIGNAL CHARACTERISTICS

| | | | | |
|--|------------|-----|-----|------------------|
| Current-Gain — Bandwidth Product ($I_C = -10 \text{ mAdc}$, $V_{CE} = -20 \text{ Vdc}$, $f = 100 \text{ MHz}$) | f_T | 250 | — | MHz |
| Output Capacitance ($V_{CB} = -5.0 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$) | C_{obo} | — | 4.5 | pF |
| Input Capacitance ($V_{EB} = -0.5 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ MHz}$) | C_{ibo} | — | 10 | pF |
| Input Impedance ($V_{CE} = -10 \text{ Vdc}$, $I_C = -1.0 \text{ mAdc}$, $f = 1.0 \text{ kHz}$) | h_{ie} | 2.0 | 12 | k Ω |
| Voltage Feedback Ratio ($V_{CE} = -10 \text{ Vdc}$, $I_C = -1.0 \text{ mAdc}$, $f = 1.0 \text{ kHz}$) | h_{re} | 0.1 | 10 | $\times 10^{-4}$ |
| Small-Signal Current Gain ($V_{CE} = -10 \text{ Vdc}$, $I_C = -1.0 \text{ mAdc}$, $f = 1.0 \text{ kHz}$) | h_{fe} | 100 | 400 | — |
| Output Admittance ($V_{CE} = -10 \text{ Vdc}$, $I_C = -1.0 \text{ mAdc}$, $f = 1.0 \text{ kHz}$) | * h_{oe} | 3.0 | 60 | μmhos |
| Noise Figure ($V_{CE} = -5.0 \text{ Vdc}$, $I_C = -100 \mu\text{Adc}$, $R_S = 1.0 \text{ k}\Omega$, $f = 1.0 \text{ kHz}$) | NF | — | 4.0 | dB |

SWITCHING CHARACTERISTICS

| | | | | | |
|--------------|---|-------|---|-----|----|
| Delay Time | ($V_{CC} = -3.0 \text{ Vdc}$, $V_{BE} = 0.5 \text{ Vdc}$, $I_C = -10 \text{ mAdc}$, $I_{B1} = -1.0 \text{ mAdc}$) | t_d | — | 35 | ns |
| Rise Time | | t_d | — | 35 | |
| Storage Time | ($V_{CC} = -3.0 \text{ Vdc}$, $I_C = -10 \text{ mAdc}$, $I_{B1} = I_{B2} = -1.0 \text{ mAdc}$) | t_s | — | 225 | ns |
| Fall Time | | t_f | — | 75 | |

 3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

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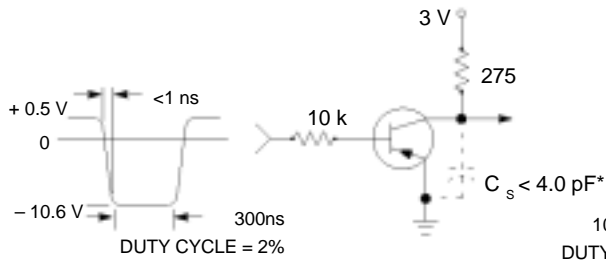


Figure 1. Delay and Rise Time Equivalent Test Circuit

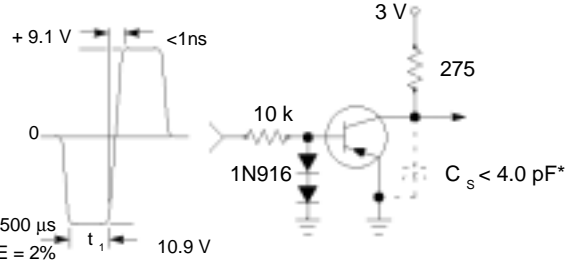


Figure 2. Storage and Fall Time Equivalent Test Circuit

*Total shunt capacitance of test jig and connectors

TYPICAL TRANSIENT CHARACTERISTICS

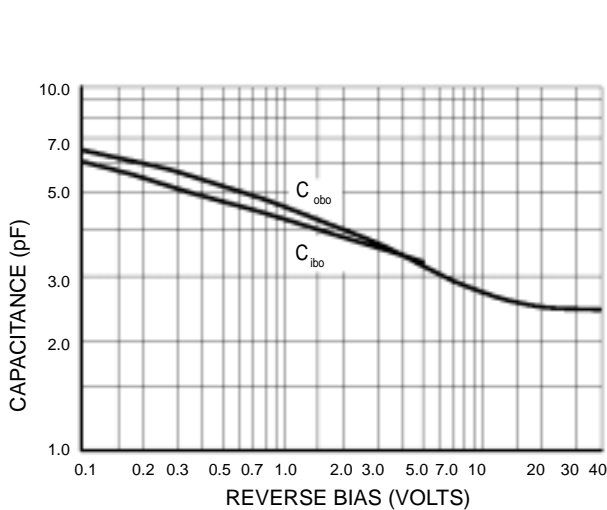


Figure 3. Capacitance

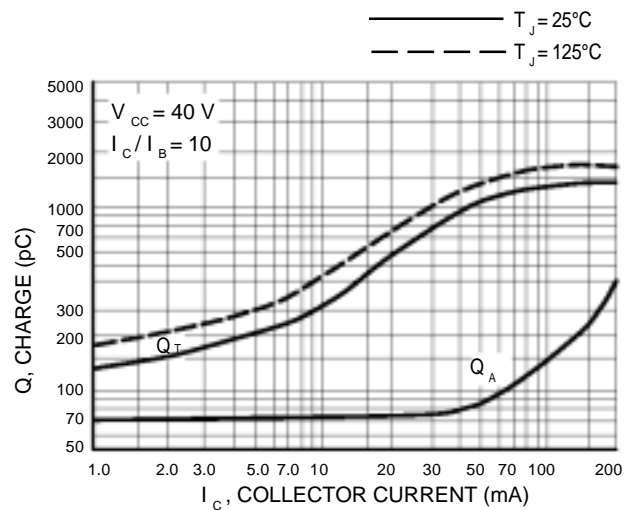


Figure 4. Charge Data

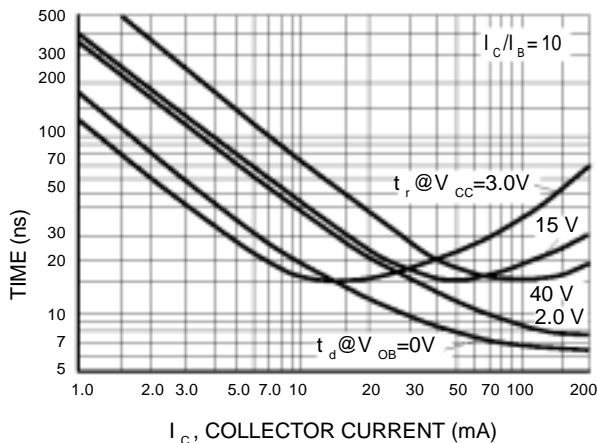


Figure 5. Turn-On Time

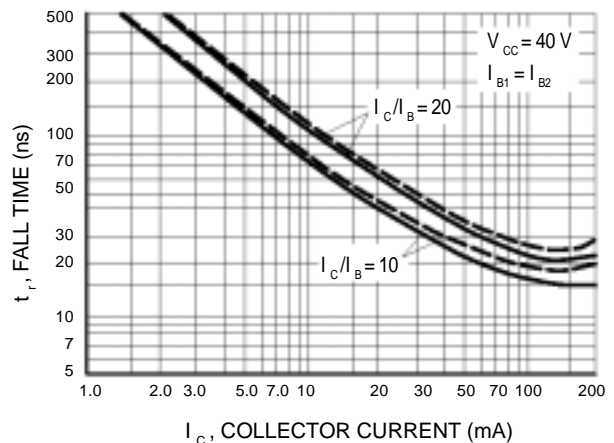


Figure 6. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

($V_{CE} = -5.0$ Vdc, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

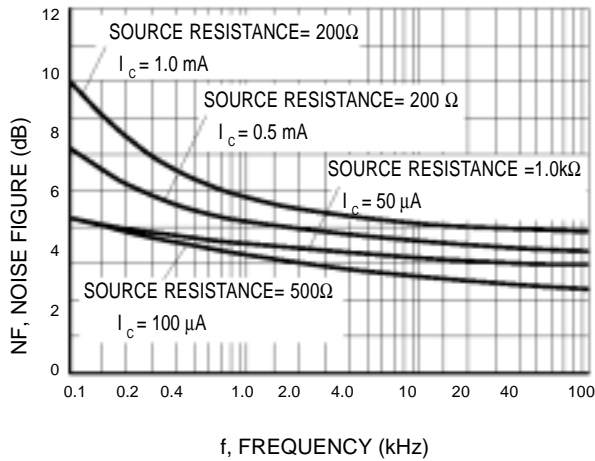


Figure 7. Noise Figure

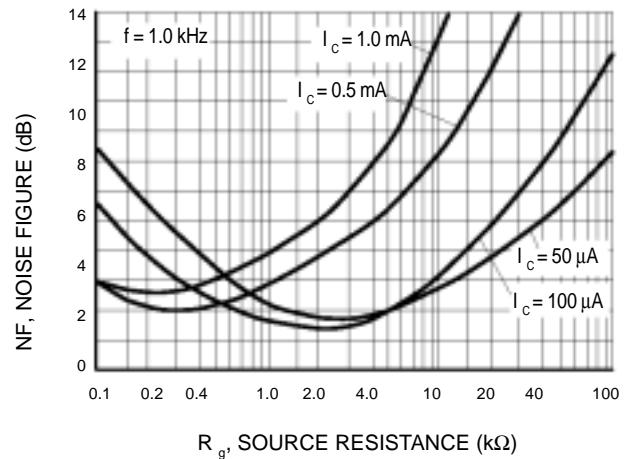


Figure 8. Noise Figure

h PARAMETERS

($V_{CE} = 10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C}$)

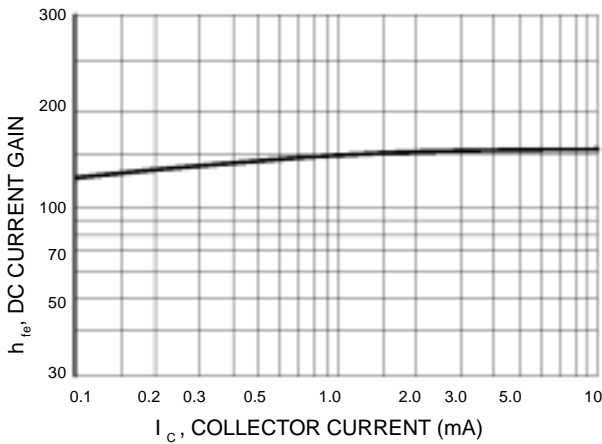


Figure 9. Current Gain

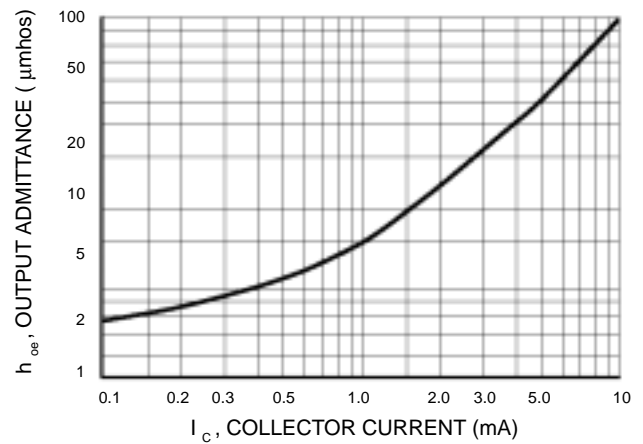


Figure 10. Output Admittance

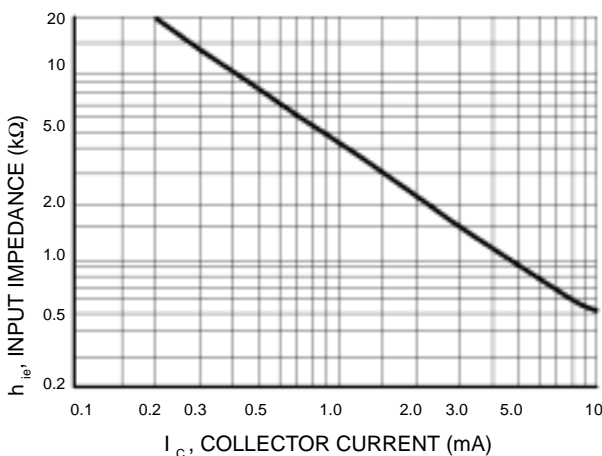


Figure 11. Input Impedance

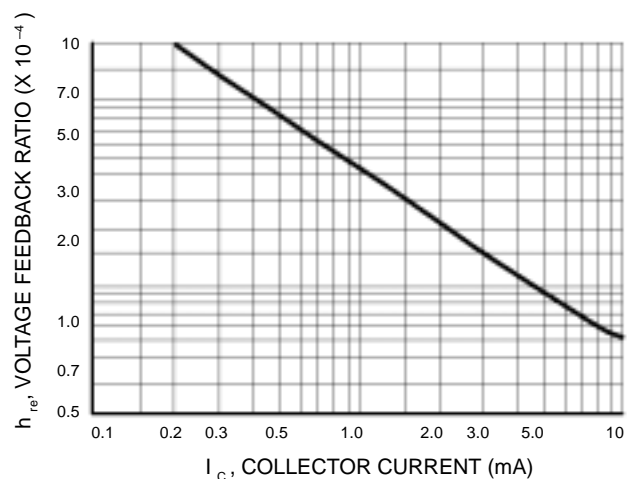


Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

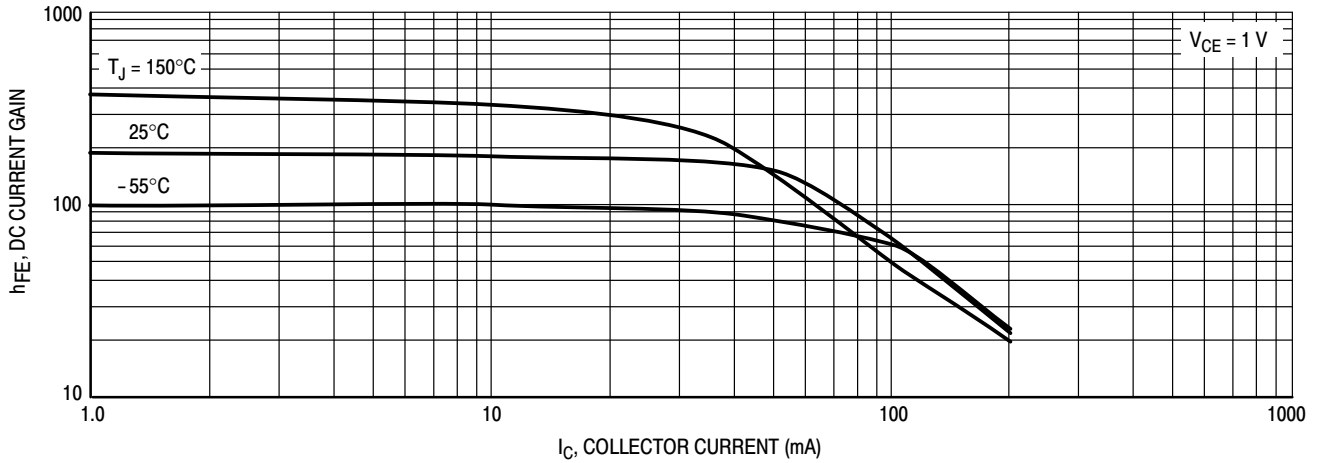


Figure 13. DC Current Gain

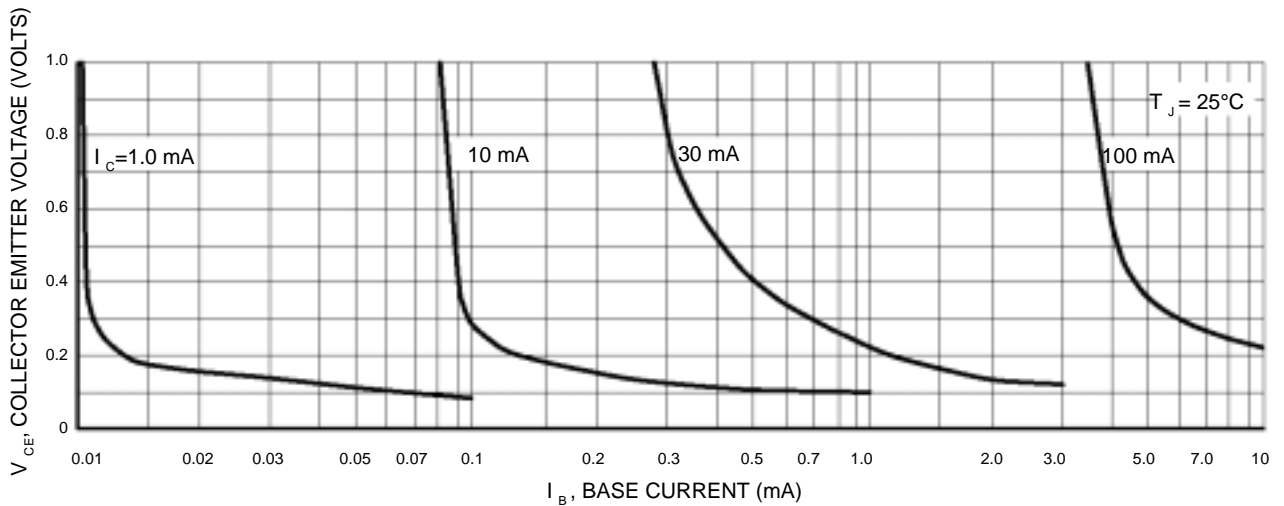


Figure 14. Collector Saturation Region

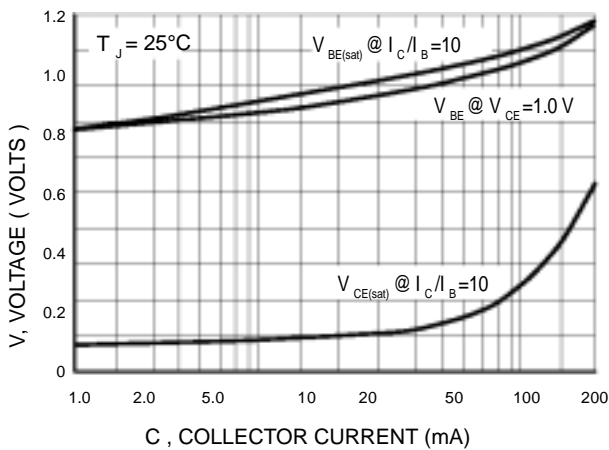


Figure 15. "ON" Voltages

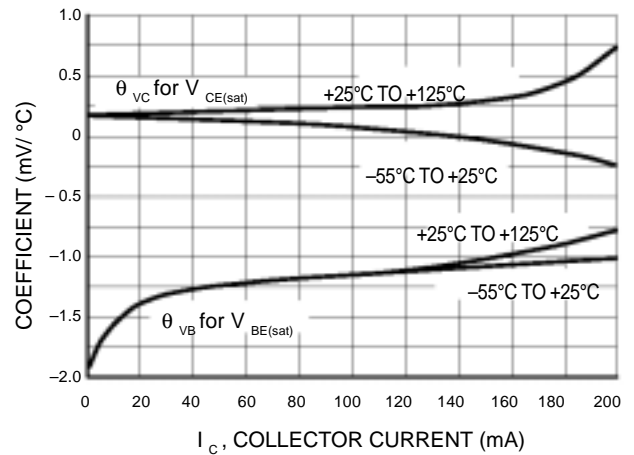
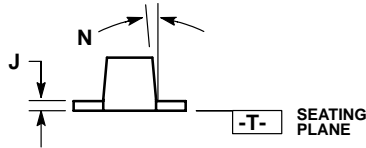
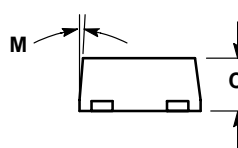
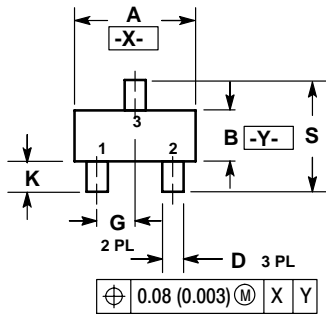


Figure 16. Temperature Coefficients

LMBT3906TT1G;S-LMBT3906TT1G

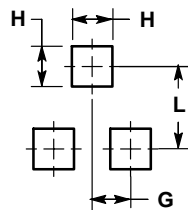
SC-89



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 463C-01 OBSOLETE, NEW STANDARD 463C-02.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|-----------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 1.50 | 1.60 | 1.70 | 0.059 | 0.063 | 0.067 |
| B | 0.75 | 0.85 | 0.95 | 0.030 | 0.034 | 0.040 |
| C | 0.60 | 0.70 | 0.80 | 0.024 | 0.028 | 0.031 |
| D | 0.23 | 0.28 | 0.33 | 0.009 | 0.011 | 0.013 |
| G | 0.50 BSC | | | 0.020 BSC | | |
| H | 0.53 REF | | | 0.021 REF | | |
| J | 0.10 | 0.15 | 0.20 | 0.004 | 0.006 | 0.008 |
| K | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.020 |
| L | 1.10 REF | | | 0.043 REF | | |
| M | --- | --- | 10 ° | --- | --- | 10 ° |
| N | --- | --- | 10 ° | --- | --- | 10 ° |
| S | 1.50 | 1.60 | 1.70 | 0.059 | 0.063 | 0.067 |



RECOMMENDED PATTERN OF SOLDER PADS

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)